

2SB857, 2SB858

Silicon PNP Triple Diffused

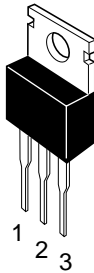
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Application

Low frequency power amplifier complementary pair with 2SD1133 and 2SD1134

Outline

TO-220AB



1. Base
2. Collector (Flange)
3. Emitter

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings		Unit
		2SB857	2SB858	
Collector to base voltage	V_{CBO}	-70	-70	V
Collector to emitter voltage	V_{CEO}	-50	-60	V
Emitter to base voltage	V_{EBO}	-5	-5	V
Collector current	I_C	-4	-4	A
Collector peak current	$I_{C(peak)}$	-8	-8	A
Collector power dissipation	P_C^{*1}	40	40	W
Junction temperature	T_j	150	150	°C
Storage temperature	T_{stg}	-45 to +150	-45 to +150	°C

Note: 1. Value at $T_C = 25^\circ\text{C}$

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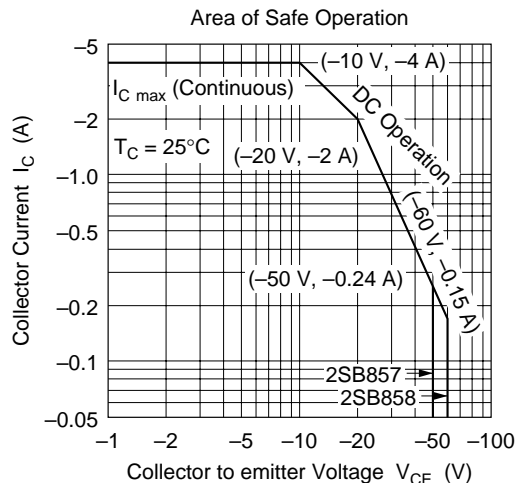
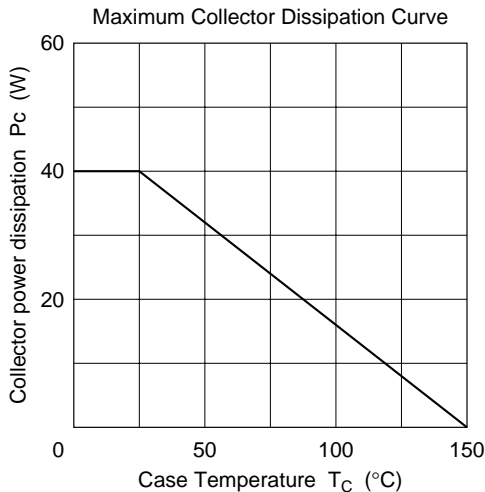
Electrical Characteristics (Ta = 25°C)

Item	Symbol	2SB857			2SB858			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	-70	—	—	-70	—	—	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-50	—	—	-60	—	—	V	$I_C = -50 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	-5	—	—	V	$I_E = -10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-1	—	—	-1	μA	$V_{CB} = -50 \text{ V}, I_E = 0$
DC current transfer ratio	h_{FE1}^{*1}	60	—	320	60	—	320		$V_{CE} =$ $I_C = -1 \text{ A}^{*2}$
	h_{FE2}	35	—	—	35	—	—		-4 V $I_C = -0.1 \text{ A}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-1	—	—	-1	V	$I_C = -2 \text{ A}, I_B = -0.2 \text{ A}^{*2}$
Base to emitter voltage	V_{BE}	—	—	-1	—	—	-1	V	$V_{CE} = -4 \text{ V}, I_C = -1 \text{ A}^{*2}$
Gain bandwidth product	f_T	—	15	—	—	15	—	MHz	$V_{CE} = -4 \text{ V}, I_C = -0.5 \text{ A}^{*2}$

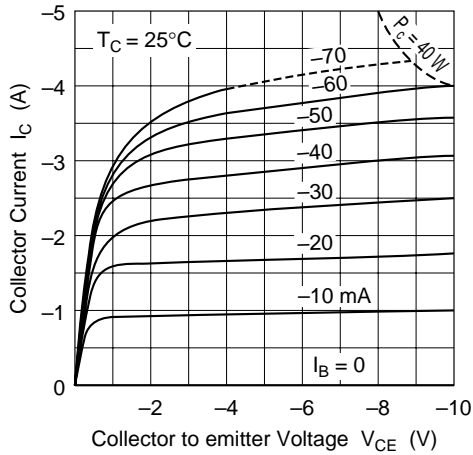
Notes: 1. The 2SB857 and 2SB858 are grouped by h_{FE1} as follows.

2. Pulse test

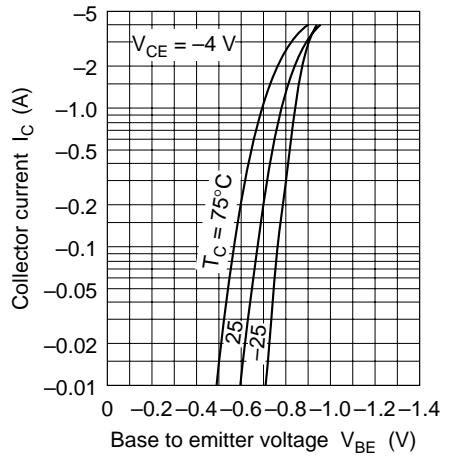
B	C	D
60 to 120	100 to 200	160 to 320



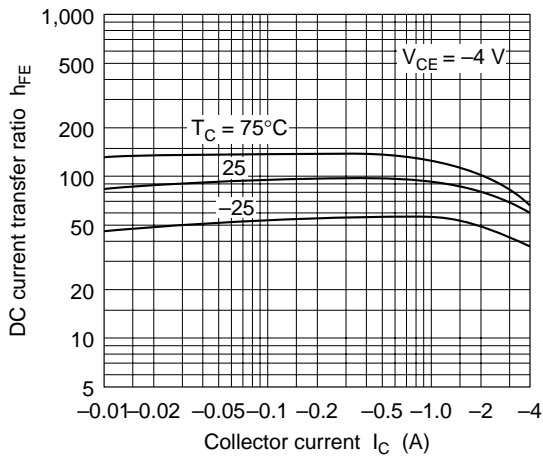
Typical Output Characteristics



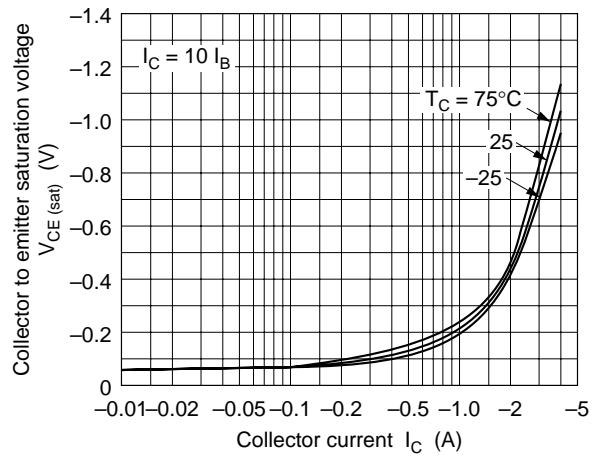
Typical Transfer Characteristics

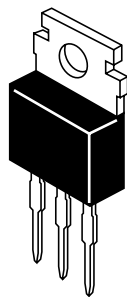
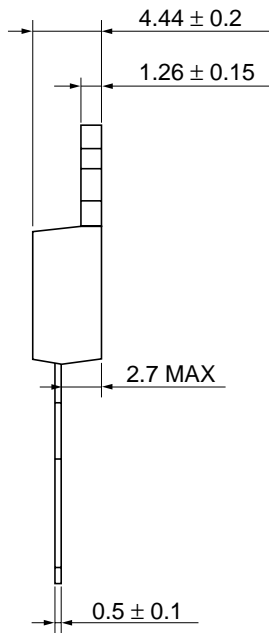
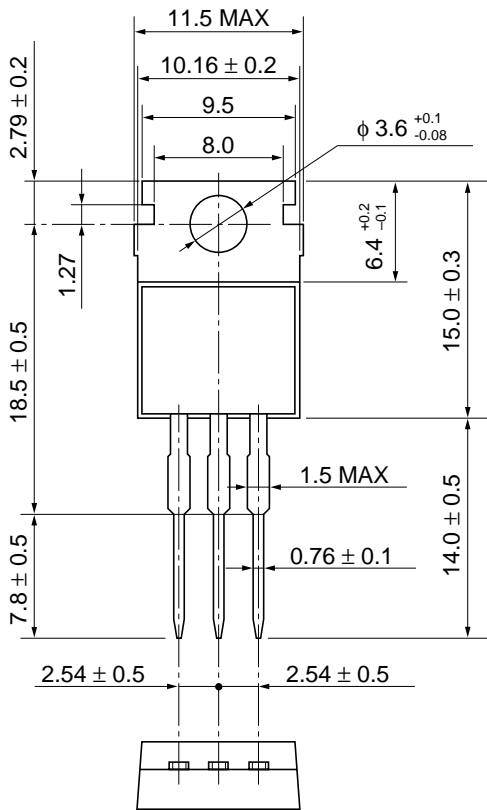


DC Current Transfer Ratio vs. Collector Current



Collector to Emitter Saturation Voltage vs. Collector Current





Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.8 g

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